

## φ100 μm IR Pin-Point LED Chip OPA8510PPS

### 1. Product Name

φ100 μm IR Pin-Point LED Chip OPA8510PPS

### 2. Absolute Maximum Ratings

Ta=25°C

Parameter	Symbol	Rating	Unit
Power Dissipation	PD	200	mW
Forward Current	IF	100	mA
Reverse Voltage	VR	3	V
Operating Temperature	Topr	-30~+100	°C
Storage Temperature	Tstg	-40~+100	°C

### 3. Electro-Optical Characteristics

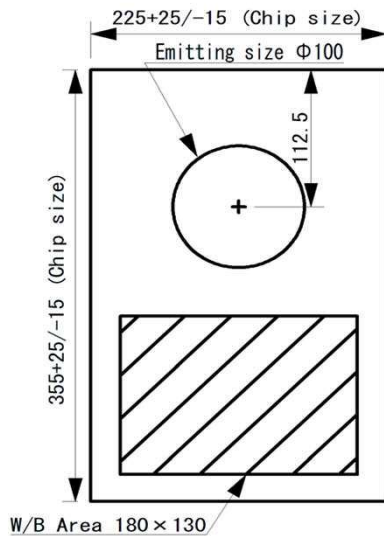
Ta=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	VF	IF=20mA	-	1.5	2.0	V
Reverse Current	IR	VR=3V	-	-	1.0	μA
Radiated Power※	Po	IF=20mA	0.85	1.10	-	mW
Peak Wavelength	λp	IF=20mA	-	850	-	nm

※ LED chip is mounted on TO-18 stem without resin coated.

Radiated Power is all light quantity that measured in integrating sphere owned by us.

### 4. Dimension (Unit: μm)

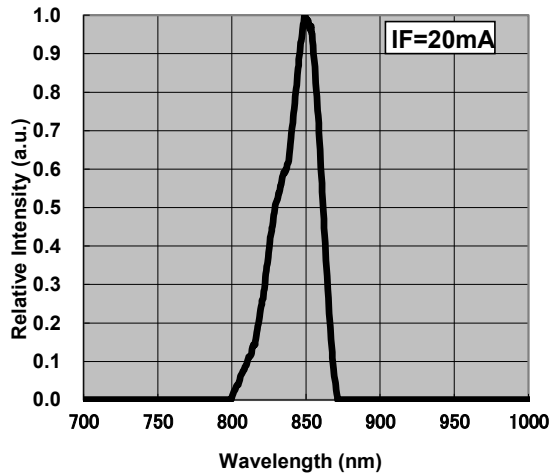


Material	AlGaAs/GaAs sub.
Emitting Surface	P Side
Surface Electrode	Au
Back Electrode	Au Alloy
Thickness	280±15 μm

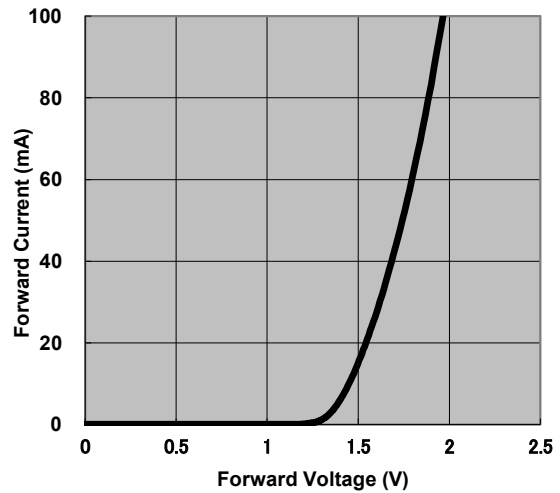
The contents of this data sheet are subject to change without advance notice for the purpose of improvement. When using this product, would you please refer to the latest specifications.

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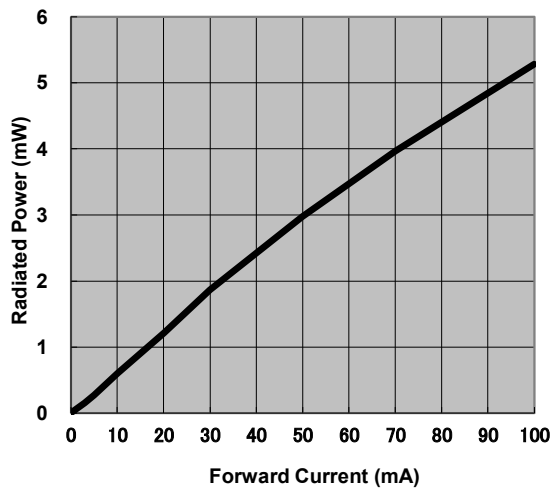
Emission Spectrum



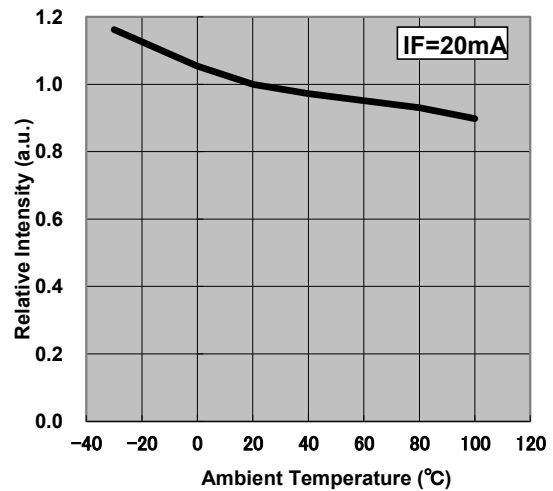
Forward Voltage vs. Forward Current



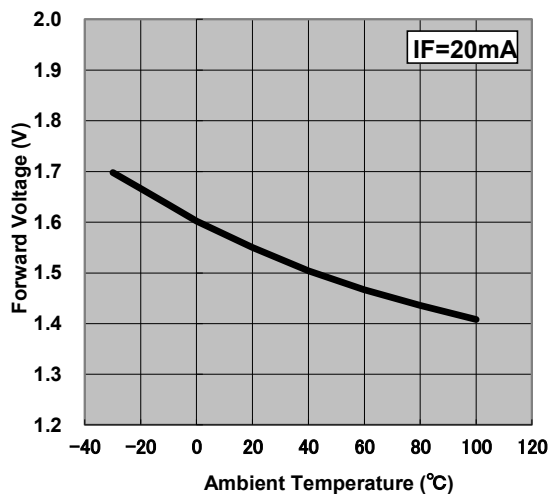
Forward Current vs. Radiated Power



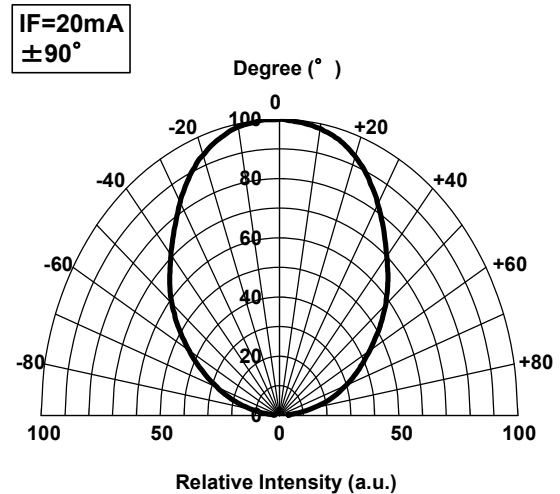
Ambient Temperature vs. Radiated Power



Ambient Temperature vs. Forward Voltage



Directivity



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